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crystallizing said semiconductor film by heating; and
forming a semiconductor island having a tapered shape by patterning said semiconductor film, said tapered shape having an angle within a range of 20° to 50° between a side thereof and an underlying surface,

wherein irradiation of laser light is performed after forming said semiconductor film.

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7. (Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film on an insulating surface;
providing a crystallization promoting material onto said semiconductor film;
crystallizing said semiconductor film by heating; and
forming a semiconductor island having a tapered shape by patterning said semiconductor film, said tapered shape having an angle within a range of 20° to 50° between a side thereof and an underlying surface,

wherein irradiation of laser light is performed after forming said semiconductor film.

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11. (Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film on an insulating surface;
crystallizing said semiconductor film by a first heating;
forming a semiconductor island having a tapered shape by patterning said semiconductor film, said tapered shape having an angle within a range of 20° to 50° between a side thereof and an underlying surface; and
forming a silicon oxide film on a surface of said semiconductor island by a second heating,

wherein irradiation of laser light is performed after forming said semiconductor film.

15. (Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film on an insulating surface;
providing a crystallization promoting material onto said semiconductor film;
crystallizing said semiconductor film by a first heating;
forming a semiconductor island having a tapered shape by patterning said semiconductor film, said tapered shape having an angle within a range of 20° to 50° between a side thereof and an underlying surface; and

forming a silicon oxide film on a surface of said semiconductor island by a second heating,

wherein irradiation of laser light is performed after forming said semiconductor film.

20. (Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film on an insulating surface;
providing a crystallization promoting material onto said semiconductor film;
crystallizing aid semiconductor film by a first heating;
forming a semiconductor island having a tapered shape by patterning said semiconductor film, said tapered shape having an angle within a range of 20° to 50° between a side thereof and an underlying surface; and

reducing said crystallization promoting material existing within said semiconductor island by a second heating,

wherein irradiation of laser light is performed after forming said semiconductor film.

26. (Amended) A method for manufacturing a thin film transistor, comprising the steps of:

forming a semiconductor film on an insulating surface;
crystallizing said semiconductor film;

forming a semiconductor island having a tapered shape by patterning said semiconductor film, said tapered shape having an angle within a range of 20° to 50° between a side thereof and an underlying surface; and

forming an insulating film on said semiconductor island,

wherein irradiation of laser light is performed after forming said semiconductor film.

27. (Amended) A method for manufacturing a thin film transistor, comprising the steps of:

forming a semiconductor film on an insulating surface;

forming a semiconductor island having a tapered shape by patterning said semiconductor film, said tapered shape having an angle within a range of 20° to 50° between a side thereof and an underlying surface; and

forming an insulating film on said semiconductor island,

wherein irradiation of laser light is performed after forming said semiconductor film.

28. (Amended) A method for manufacturing a thin film transistor, comprising the steps of:

forming a semiconductor film on an insulating surface;

crystallizing said semiconductor film; and

forming a semiconductor island having a tapered shape by patterning said semiconductor film, said tapered shape having an angle within a range of 20° to 50° between a side thereof and an underlying surface,

wherein irradiation of laser light is performed after forming said semiconductor film.

REMARKS

The Official Action mailed February 19, 2002 has been received and its contents carefully noted. Claims 1-34 are pending in the present application. Independent